Press Contacts:

Eileen Elam
KJ Communications (in the U.S. for ISi)
Tel: +1 408 927-7753
eileen@kjcompr.com

Nick Foot
Billings PR (in Europe for ISi)
Tel: +44 1491 636393
nick.foot@billings-europe.com

MEDIA ADVISORY

Z-RAM: A Better DRAM

Innovative Silicon's Jeff Mitchell to Outline Details at International SoC Conference

SANTA CLARA, Calif., — October 31, 2008 — Innovative Silicon, Inc. (ISi), developer of the Z-RAM® zero-capacitor floating body memory technology, today announced that Jeff Mitchell, director of technical marketing, is giving a presentation titled "Z-RAM: A Better DRAM" at the International SoC Conference.

Where: Radisson Hotel Newport Beach
4545 MacArthur Blvd.
Newport Beach, CA 92660

When: Thursday, November 6, 2008 from 9:15 – 9:45

During the presentation, Mitchell will uncover challenges facing the evolution of DRAM and outline the next frontier--floating body memory. He will also detail how ISi's floating body implementation, Z-RAM, leverages the Bipolar Optimized Storage Transistor (BOOST™) to achieve large programming windows and longer retention times. Attendees at the conference will also gain new insight into DRAM, and why the 40 year-old technology cannot readily scale to designs at 32nm and below.

About the International SoC Conference
In less than six years, the annual International SoC Conference has become the premier event for the engineering communities that are involved in new SoC, ASIC, CSSP, ASSP, and FPGA-based designs or are working with Foundry Services on a worldwide basis. For more information see http://www.SoCconference.com

About Innovative Silicon

Innovative Silicon, Inc. (ISi) is the inventor and licensor of the Z-RAM® ultra-dense memory technology for stand-alone DRAM and embedded memory applications. Z-RAM is the world's lowest-cost semiconductor memory technology – simpler to manufacture than DRAM, and a fraction the size of SRAM. ISi and the Z-RAM technology have received numerous industry awards, including the World Economic Forum's selection of ISi as a 2008 Technology Pioneer, and IEEE Spectrum Magazine's selection of Z-RAM as the 2007 "Emerging Technology Most Likely to Succeed." Z-RAM is a "Zero Capacitor," true single-transistor floating body memory that eliminates the complex capacitor found in today's DRAM technologies – a fundamental roadblock to Moore's Law of scaling. Z-RAM provides semiconductor manufacturers a solution for nanoscale manufacturing processes that can dramatically lower semiconductor costs. The Z-RAM memory technology has been licensed by Hynix Semiconductor for use in its DRAM chips, and by AMD for use in microprocessors. Since 2003, the company has closed three funding rounds totaling $47 million, received over 30 patents on the technology, developed test chips in multiple technologies from 90nm to 32nm, and has established global R&D, engineering and support centers in Europe, Asia and North America. For more information see www.z-ram.com.

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